**24 November 2023** 

Product data sheet

## 1. General description

100 mA NPN Resistor-Equipped Transistor (RET) in an ultra small DFN1110D-3 (SOT8015) leadless Surface-Mounted Device (SMD) plastic package with side-wettable flanks.

PNP complement: PDTA123YQB

### 2. Features and benefits

- 100 mA output current capability
- Built-in resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Low package height of 0.5 mm
- Suitable for Automatic Optical Inspection (AOI) of solder joint

# 3. Applications

- Digital applications
- · Cost saving alternative for BC847 series in digital applications
- Controlling IC inputs
- Switching loads

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	50	V
Io	output current			-	-	100	mA
R1	bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ
R2/R1	bias resistor ratio		[1]	3.6	4.5	5.5	

[1] See "Section 11: Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2: 10 k $\Omega$ 

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	GND	ground (emitter)	3	
3	0	output (collector)	Transparent top view DFN1110D-3 (SOT8015)	GND R2 R2 R2 R2 R2

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	ackage				
	Name	Description	Version			
PDTC123YQB	DFN1110D-3	plastic, leadless extremely thin small outline package with side-wettable flanks (SWF); 3 terminals; 0.65 mm pitch; 1.1 mm x 1 mm x 0.48 mm body	SOT8015			

# 7. Marking

### Table 4. Marking codes

Type number	Marking code
PDTC123YQB	QE

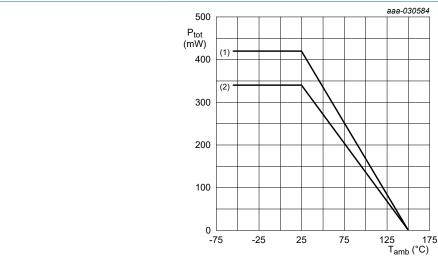
# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	50	V
$V_{CEO}$	collector-emitter voltage	open base		-	50	V
$V_{EBO}$	emitter-base voltage	open collector		-	5	V
VI	input voltage			-5	12	V
Io	output current			-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	340	mW
			[2]	-	420	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided; 70 µm copper; tin-plated and standard footprint.



- (1) FR4 PCB, single-sided 70 µm copper, standard footprint
- (2) FR4 PCB, single-sided 35 µm copper, standard footprint

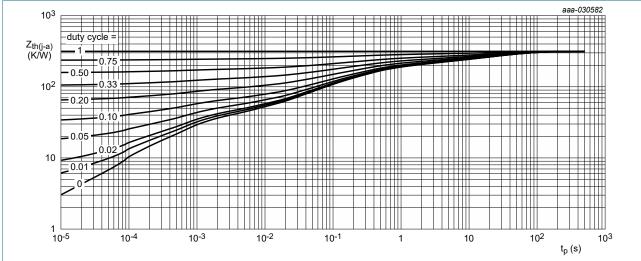
Fig. 1. Power derating curve SOT8015 (DFN1110D-3)

## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

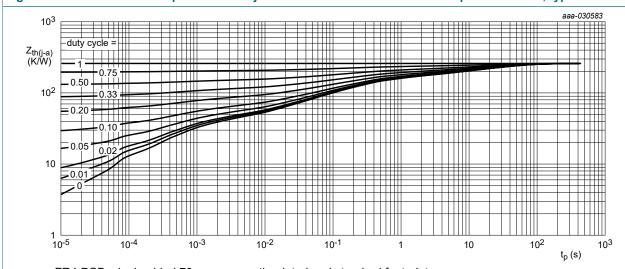
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uity-a)	thermal resistance from	in free air	[1]	-	-	368	K/W
	junction to ambient		[2]	-	-	298	K/W

- [1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB; single-sided; 70 µm copper; tin-plated and standard footprint.



FR4 PCB, single-sided 35 µm copper, tin-plated and standard footprint

Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, single-sided 70 µm copper, tin-plated and standard footprint

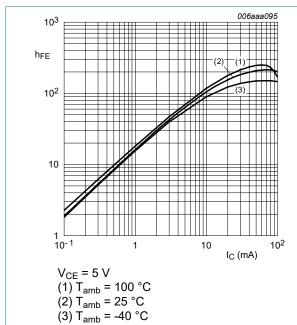
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 10. Characteristics

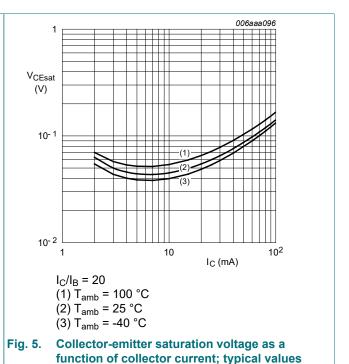
**Table 7. Characteristics** 

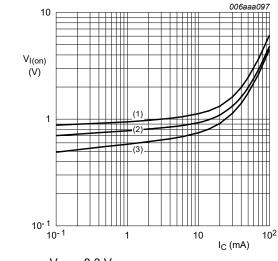
Parameter	Conditions		Min	Тур	Max	Unit
collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		50	-	-	V
collector-base cut-off current	<sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
collector-emitter cut-off	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	5	μΑ
emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	700	μΑ
DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA; T <sub>amb</sub> = 25 °C		35	-	-	
collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	mV
off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}; T_{amb} = 25 \text{ °C}$		-	0.75	0.3	V
on-state input voltage	$V_{CE}$ = 300 mV; $I_{C}$ = 20 mA; $T_{amb}$ = 25 °C		2.5	1.15	-	V
bias resistor 1 (input)		[1]	1.54	2.2	2.86	kΩ
bias resistor ratio		[1]	3.6	4.5	5.5	
collector capacitance	$V_{CB}$ = 10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; f = 1 MHz; $T_{amb}$ = 25 °C		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[2]	-	230	-	MHz
	collector-base breakdown voltage collector-emitter breakdown voltage collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance	collector-base breakdown voltage $I_{C} = 100 \; \mu \text{A}; \; I_{E} = 0 \; \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ collector-emitter breakdown voltage $I_{C} = 2 \; \text{mA}; \; I_{B} = 0 \; \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ collector-base cut-off current $V_{CB} = 50 \; \text{V}; \; I_{E} = 0 \; \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ collector-emitter cut-off current $V_{CE} = 30 \; \text{V}; \; I_{B} = 0 \; \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ $V_{CE} = 30 \; \text{V}; \; I_{B} = 0 \; \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ emitter-base cut-off current $V_{CE} = 5 \; \text{V}; \; I_{C} = 0 \; \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ collector-emitter saturation voltage $V_{CE} = 5 \; \text{V}; \; I_{C} = 5 \; \text{mA}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ collector-emitter saturation voltage $V_{CE} = 5 \; \text{V}; \; I_{C} = 100 \; \mu \text{A}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ on-state input voltage $V_{CE} = 300 \; \text{mV}; \; I_{C} = 20 \; \text{mA}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ bias resistor 1 (input) bias resistor ratio $V_{CB} = 10 \; \text{V}; \; I_{E} = 0 \; \text{A}; \; I_{e} = 0 \; \text{A}; \; f = 1 \; \text{MHz}; \; T_{amb} = 25 \; ^{\circ}\text{C}$ transition frequency $V_{CE} = 5 \; \text{V}; \; I_{C} = 10 \; \text{mA}; \; f = 100 \; \text{MHz};$	collector-base breakdown voltage	collector-base breakdown voltage $I_C = 100~\mu A; I_E = 0~A; T_{amb} = 25~^{\circ}C$ 50 collector-emitter breakdown voltage $I_C = 2~mA; I_B = 0~A; T_{amb} = 25~^{\circ}C$ 50 collector-base cut-off current $V_{CB} = 50~V; I_E = 0~A; T_{amb} = 25~^{\circ}C$ - collector-emitter cut-off current $V_{CE} = 30~V; I_B = 0~A; T_{amb} = 25~^{\circ}C$ - cemitter-base cut-off current $V_{CE} = 30~V; I_B = 0~A; T_{amb} = 25~^{\circ}C$ - cemitter-base cut-off current $V_{CE} = 5~V; I_C = 0~A; T_{amb} = 25~^{\circ}C$ - collector-emitter saturation voltage $I_C = 10~mA; I_B = 0.5~mA; T_{amb} = 25~^{\circ}C$ - con-state input voltage $V_{CE} = 5~V; I_C = 100~\mu A; T_{amb} = 25~^{\circ}C$ - con-state input voltage $V_{CE} = 5~V; I_C = 100~\mu A; T_{amb} = 25~^{\circ}C$ - con-state input voltage $V_{CE} = 300~mV; I_C = 20~mA; T_{amb} = 25~^{\circ}C$ bias resistor 1 (input) [1] 1.54 bias resistor ratio $V_{CB} = 10~V; I_E = 0~A; I_E = 0~A; I_E = 1~MHz; T_{amb} = 25~^{\circ}C$ transition frequency $V_{CE} = 5~V; I_C = 10~mA; I_E = 0~A; I_E =$	collector-base breakdown voltage $I_C = 100  \mu A; I_E = 0  A; T_{amb} = 25  ^{\circ}C$ 50       -         collector-emitter breakdown voltage $I_C = 2  \text{mA}; I_B = 0  A; T_{amb} = 25  ^{\circ}C$ 50       -         collector-base cut-off current $V_{CB} = 50  V; I_E = 0  A; T_{amb} = 25  ^{\circ}C$ -       -         collector-emitter cut-off current $V_{CE} = 30  V; I_B = 0  A; T_{amb} = 25  ^{\circ}C$ -       -         emitter-base cut-off current $V_{CE} = 30  V; I_C = 0  A; T_{amb} = 25  ^{\circ}C$ -       -         DC current gain $V_{CE} = 5  V; I_C = 5  mA; T_{amb} = 25  ^{\circ}C$ 35       -         collector-emitter saturation voltage $I_C = 10  \text{mA}; I_B = 0.5  \text{mA}; T_{amb} = 25  ^{\circ}C$ -       -         off-state input voltage $V_{CE} = 5  V; I_C = 100  \mu A; T_{amb} = 25  ^{\circ}C$ -       0.75         on-state input voltage $V_{CE} = 300  \text{mV}; I_C = 20  \text{mA};$ 2.5       1.15         bias resistor 1 (input)       [1] 1.54 2.2         bias resistor ratio       [1] 3.6 4.5         collector capacitance $V_{CB} = 10  V; I_C = 10  \text{mA}; I_C = $	collector-base breakdown voltage $I_C = 100  \mu A;  I_E = 0  A;  T_{amb} = 25  ^{\circ}C$ 50         -         -           collector-emitter breakdown voltage $I_C = 2  \text{mA};  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ 50         -         -           collector-base cut-off current $V_{CB} = 50  V;  I_E = 0  A;  T_{amb} = 25  ^{\circ}C$ -         -         100           collector-emitter cut-off current $V_{CE} = 30  V;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ -         -         100           emitter-base cut-off current $V_{CE} = 30  V;  I_B = 0  A;  T_{amb} = 25  ^{\circ}C$ -         -         700           DC current gain $V_{CE} = 5  V;  I_C = 0  A;  T_{amb} = 25  ^{\circ}C$ 35         -         -           collector-emitter saturation voltage $I_C = 10  \text{mA};  I_B = 0.5  \text{mA};  T_{amb} = 25  ^{\circ}C$ -         -         150           off-state input voltage $V_{CE} = 5  V;  I_C = 100  \mu A;  T_{amb} = 25  ^{\circ}C$ -         0.75         0.3           on-state input voltage $V_{CE} = 300  \text{mV};  I_C = 20  \text{mA};$ 2.5         1.15         -           bias resistor 1 (input)         [1]         1.54         2.2         2.86           bias resistor ratio $V_{CE} = 10  V;  I_C = 0  A;  I_C = 0  A;  I_C =$

- [1] See "Section 11: Test information" for resistor calculation and test conditions.
- [2] Characteristics of built-in transistor.



g. 4. DC current gain as a function of collector current; typical values

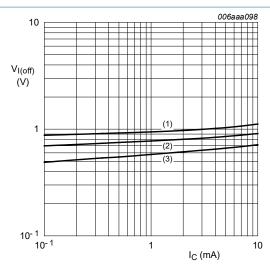




 $V_{CE} = 0.3 V$ 

(1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Fig. 6. On-state input voltage as a function of collector | Fig. 7. current; typical values



V<sub>CE</sub> = 5 V (1) T<sub>amb</sub> = -40 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = 100 °C

Off-state input voltage as a function of collector current; typical values

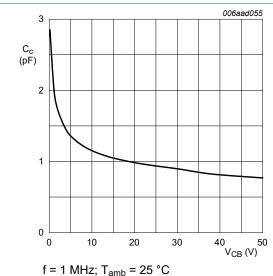
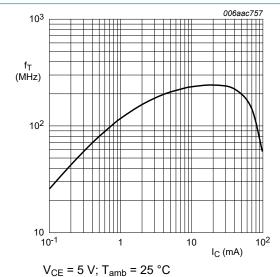


Fig. 8. Collector capacitance as a function of collector- Fig. 9. base voltage; typical values of built-in transistor



Transition frequency as a function of collector current; typical values of built-in transistor

# 11. Test information

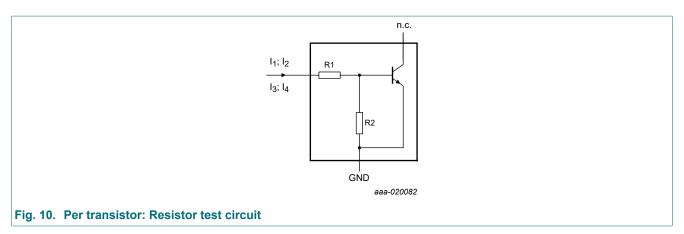
#### **Resistor calculation**

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{1})}{I_{2} - I_{1}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

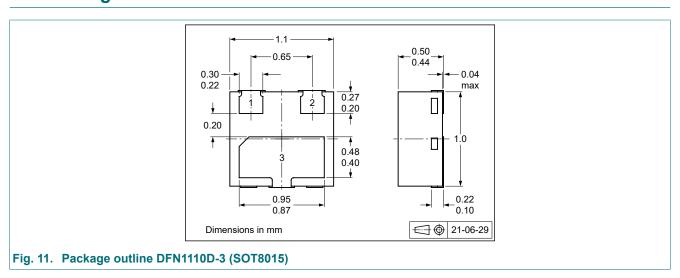


### **Resistor test conditions**

Table 8. Resistor test conditions

Type number	R1 (kΩ)	R2 (kΩ)	Test conditions	Test conditions		
			I <sub>1</sub>	l <sub>2</sub>	l <sub>3</sub>	14
PDTC123YQB	2.2	10	1300 µA	1500 µA	-350 μΑ	-450 μA

# 12. Package outline



50 V, 100 mA NPN resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2: 10 k $\Omega$ 

# 13. Soldering

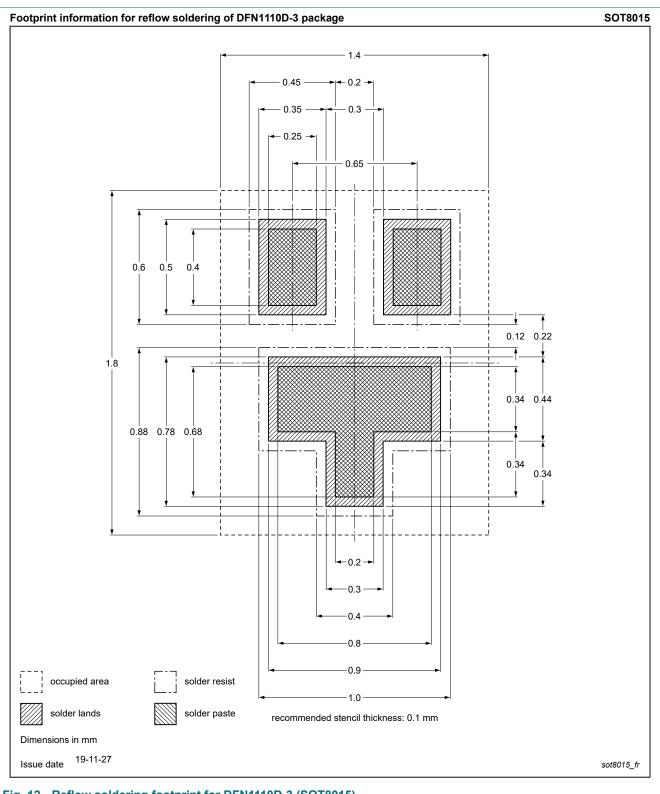


Fig. 12. Reflow soldering footprint for DFN1110D-3 (SOT8015)

50 V, 100 mA NPN resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2: 10 k $\Omega$ 

# 14. Revision history

## Table 9. Revision history

Data sheet ID	Release date		Change notice	Supersedes
PDTC123YQB v.1	20231124	Product data sheet	-	-

#### 50 V, 100 mA NPN resistor-equipped transistor; R1 = 2.2 kΩ, R2: 10 kΩ

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PDTC123YQB

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### 50 V, 100 mA NPN resistor-equipped transistor; R1 = 2.2 k $\Omega$ , R2: 10 k $\Omega$

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For more information, please visit: http://www.nexperia.com
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Date of release: 24 November 2023

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